VS-10ETS08FP-M3, VS-10ETS12FP-M3

Vishay Semiconductors

ROHS

HALOGEN

FREE

High Voltage, Input Rectifier Diode, 10 A



PRIMARY CHARACTERISTICS				
I _{F(AV)}	10 A			
V_{R}	800 V to 1200 V			
V _F at I _F	1.1 V			
I _{FSM}	160 A			
T _J max.	150 °C			
Package	TO-220 FullPAK 2L			
Circuit configuration	Single			

FEATURES

- · Very low forward voltage drop
- 150 °C max. operating junction temperature
- · Glass passivated pellet chip junction
- Designed and qualified according to JEDEC®-JESD 47
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- · Input rectification
- Vishay Semiconductors switches and output rectifiers which are available in identical package outlines

DESCRIPTION

High voltage rectifiers optimized for very low forward voltage drop with moderate leakage.

These devices are intended for use in main rectification (single or three phase bridge).

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS				
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C common heatsink of 1 °C/W	12.0	16.0	А		

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Sinusoidal waveform	10	А			
V _{RRM}	Range	800, 1200	V			
I _{FSM}		160	Α			
V _F	10 A, T _J = 25 °C	1.1	V			
TJ		-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA			
VS-10ETS08FP-M3	800	900	0.5			
VS-10ETS12FP-M3	1200	1300	0.5			



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	I _{F(AV)}	T _C = 105 °C, 180° conduction half sine wave	10	
Maximum peak one cycle	,	10 ms sine pulse, rated V _{RRM} applied	135	Α
non-repetitive surge current	IFSM	10 ms sine pulse, no voltage reapplied	160	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied	91	A ² s
	1-1	10 ms sine pulse, no voltage reapplied	130	A-S
Maximum I ² √t for fusing	I²√t	$12\sqrt{t}$ $t = 0.1$ ms to 10 ms, no voltage reapplied		A²√s

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS VALUES		UNITS	
Maximum forward voltage drop	V_{FM}	10 A, T _J = 25 °C		1.1	V
Forward slope resistance	r _t	T _{.1} = 150 °C		20	m $Ω$
Threshold voltage	V _{F(TO)}			0.82	V
Maximum valueres laskage surrent	1	T _J = 25 °C	V - Potod V	0.05	mA
Maximum reverse leakage current I _{RM}		T _J = 150 °C	V _R = Rated V _{RRM}	0.50	IIIA

THERMAL - MECH	THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and stor temperature range	age	T _J , T _{Stg}		-40 to +150	°C
Maximum thermal resistant junction to case	ce,	R_{thJC}	DC operation	2.5	
Maximum thermal resistant junction to ambient	ce,	R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf · cm
Mounting torque maximum				12 (10)	(lbf \cdot in)
Maddan dada			On a state TO 000 F HDAK 01	10ETS08FP	
Marking device			Case style TO-220 FullPAK 2L 10ETS		S12FP

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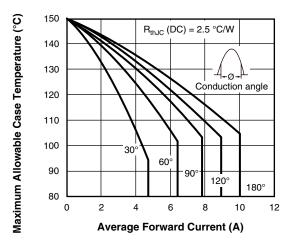


Fig. 1 - Current Rating Characteristics

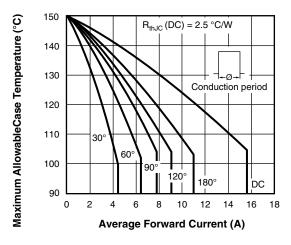


Fig. 2 - Current Rating Characteristics

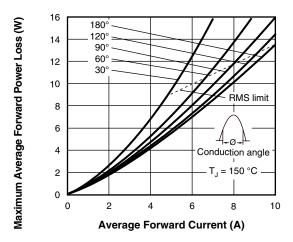


Fig. 3 - Forward Power Loss Characteristics

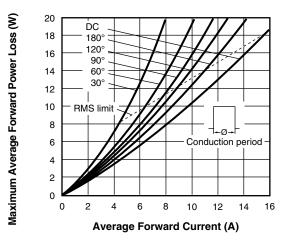


Fig. 4 - Forward Power Loss Characteristics

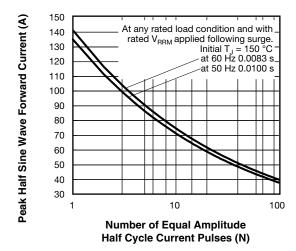


Fig. 5 - Maximum Non-Repetitive Surge Current

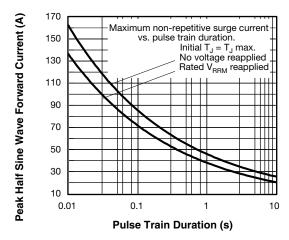


Fig. 6 - Maximum Non-Repetitive Surge Current

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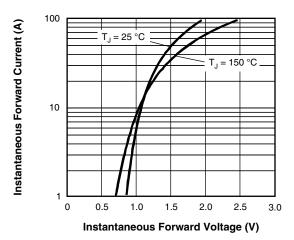


Fig. 7 - Forward Voltage Drop Characteristics

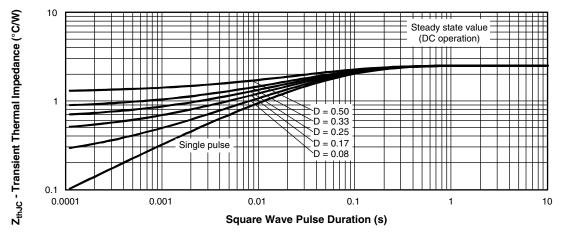


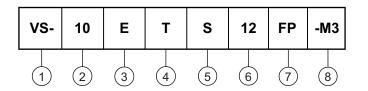
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (10 = 10 A)

Circuit configuration:

E = single diode

4 - Package:

T = TO-220

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating — 08 = 800 V

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

12 = 1200 V

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-10ETS08FP-M3	50	1000	Antistatic plastic tubes		
VS-10ETS12FP-M3	50	1000	Antistatic plastic tubes		

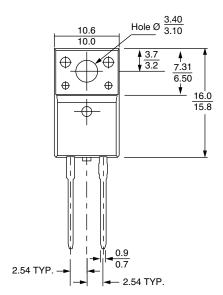
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96157
Part marking information	www.vishay.com/doc?95392

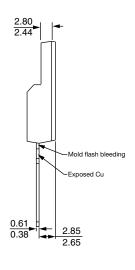


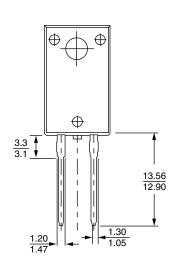
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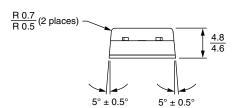
2L TO-220 FullPAK

DIMENSIONS in millimeters









Bottom view



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